NOT RECOMMENDED FOR NEW DESIGN
CONTACT US

DMG8N65SCT

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$	Package	I_D T_C = +25°C
650V	1.3Ω@V_{GS} = 10V	TO220AB (Type TH)	8A

Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high-efficiency power management applications.

Applications

- Motor Control
- Backlighting
- DC-DC Converters
- Power Management Functions

Features

- Low Input Capacitance
- High BV_{DSS} Rating for Power Application
- Low Input/Output Leakage
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

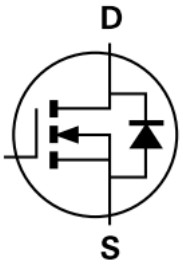
Mechanical Data

- Case: TO220AB (Type TH)
- Case Material: Molded Plastic, "Green" Molding Compound, UL Flammability Classification Rating 94V-0
- Terminals: Matte Tin Finish Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram Below
- Weight: 1.85 grams (Approximate)

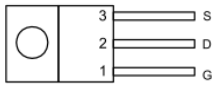
TO220AB (Type TH)

Top View

Bottom View



Equivalent Circuit



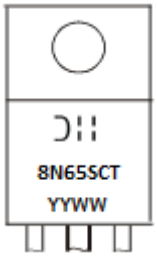
Top View
Pin Out Configuration

Ordering Information (Note 4)

Part Number	Case	Packaging
DMG8N65SCT	TO220AB (Type TH)	50 Pieces/Tube

Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



=Manufacturer's Marking
8N65SCT = Product Type Marking Code
YYWW = Date Code Marking
YY or $\underline{YY}$ = Last Two Digits of Year (ex: 17 = 2017)
WW or $\underline{WW}$ = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	650	V
Gate-Source Voltage			V_{GSS}	±30	V
Continuous Drain Current V_{GS} = 10V	Steady State	T_C = +25°C T_C = +100°C	I_D	8.0 3.8	A
Maximum Body Diode Forward Current (Note 5)			I_S	12	A
Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%)			I_{DM}	12	A
Avalanche Current, L = 60mH (Note 7)			I_{AS}	3.6	A
Avalanche Energy, L = 60mH (Note 7)			E_{AS}	389	mJ
Peak Diode Recovery dv/dt			dv/dt	5	V/ns

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation	T_C = +25°C	P_D	125	W
	T_C = +100°C		50	
Thermal Resistance, Junction to Ambient (Note 6)		$R_{\theta JA}$	54	°C/W
Thermal Resistance, Junction to Case		$R_{\theta JC}$	1	
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	650	—	—	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 650V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	100	nA	V_{GS} = ±30V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	3	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.9	1.3	Ω	V_{GS} = 10V, I_D = 4A
Diode Forward Voltage	V_{SD}	—	0.87	1.5	V	V_{GS} = 0V, I_S = 8A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C_{iss}	—	1,217	—	pF	V_{DS} = 25V, f = 1.0MHz, V_{GS} = 0V
Output Capacitance	C_{oss}	—	115	—		
Reverse Transfer Capacitance	C_{rss}	—	12	—		
Gate Resistance	R_G	—	1.24	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz
Total Gate Charge	Q_g	—	30	—	nC	V_{DD} = 520V, I_D =8A, V_{GS} = 10V
Gate-Source Charge	Q_{gs}	—	4.8	—		
Gate-Drain Charge	Q_{gd}	—	13.3	—		
Turn-On Delay Time	$t_{D(ON)}$	—	23	—	ns	V_{DD} = 450V, R_G = 25Ω, I_D =8A, V_{GS} = 10V
Turn-On Rise Time	t_R	—	46	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	115	—		
Turn-Off Fall Time	t_F	—	52	—		
Body Diode Reverse Recovery Time	t_{RR}	—	296	—	ns	di/dt = 100A/µs, V_{DS} = 100V, I_F = 8A
Body Diode Reverse Recovery Charge	Q_{RR}	—	2.7	—	µC	

Notes:
5. Device mounted on infinite heatsink.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
7. Guaranteed by design. Not subject to production testing.
8. Short duration pulse test used to minimize self-heating effect.

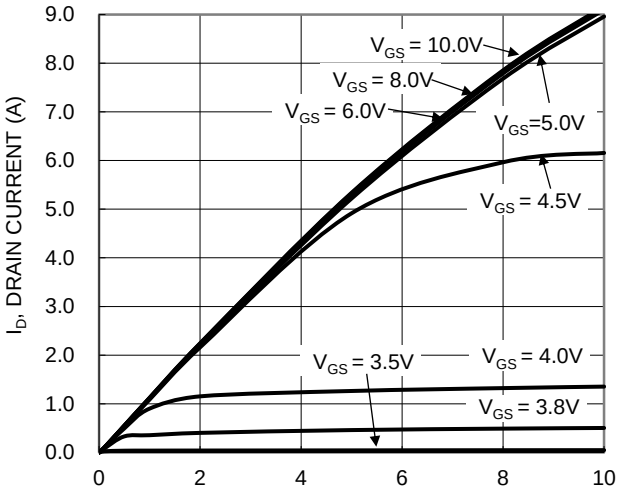


Figure 1. Typical Output Characteristic

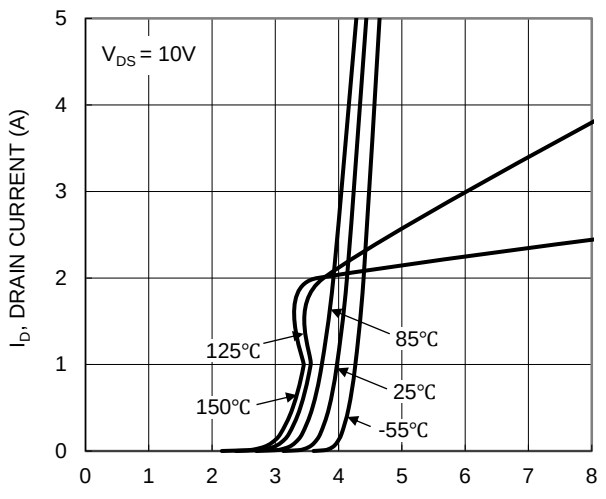


Figure 2. Typical Transfer Characteristic

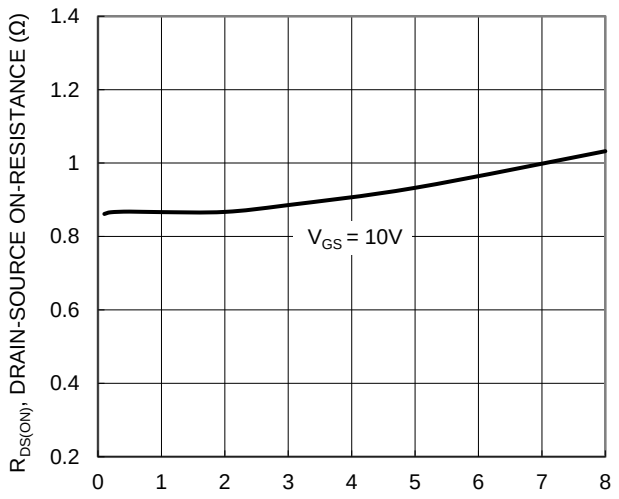


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

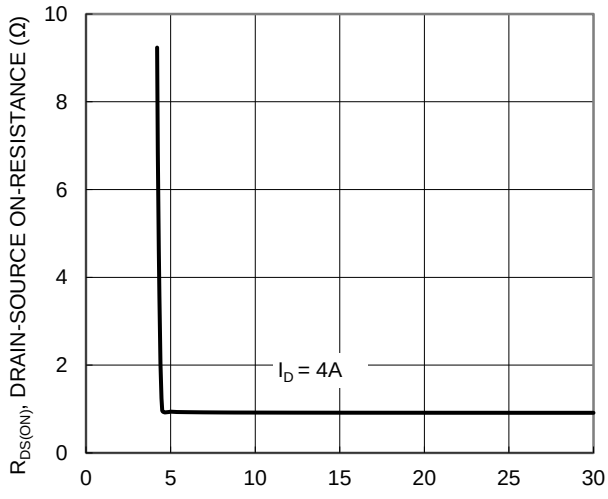


Figure 4. Typical Transfer Characteristic

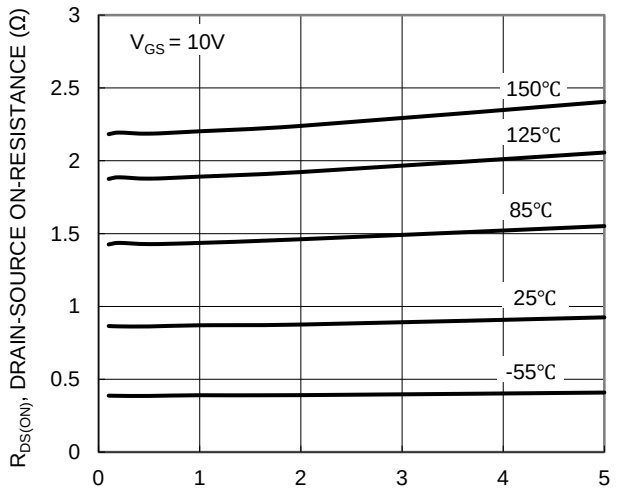


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

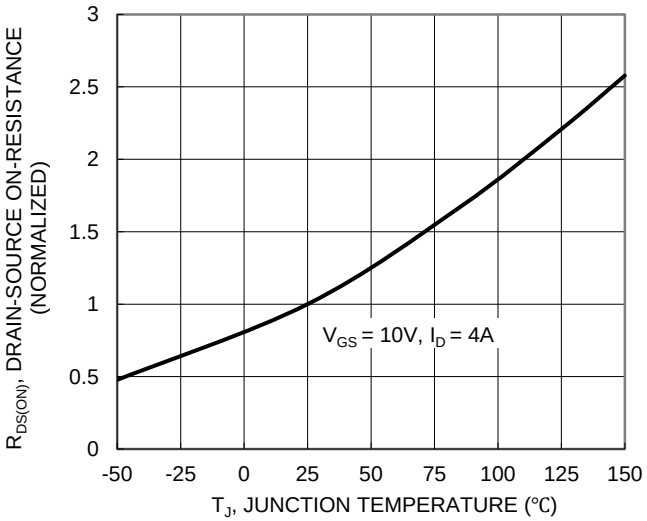


Figure 6. On-Resistance Variation with Junction Temperature

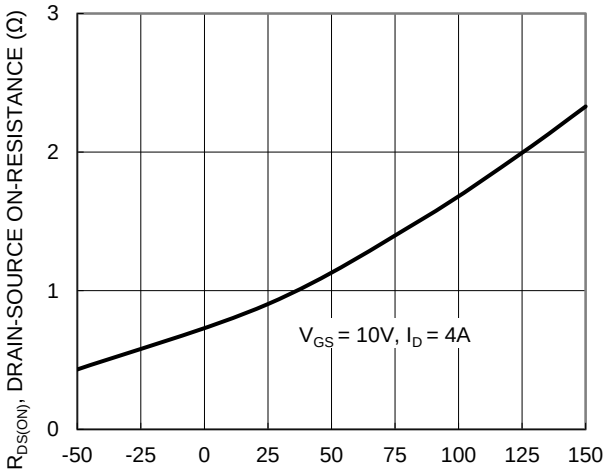


Figure 7. On-Resistance Variation with Junction Temperature

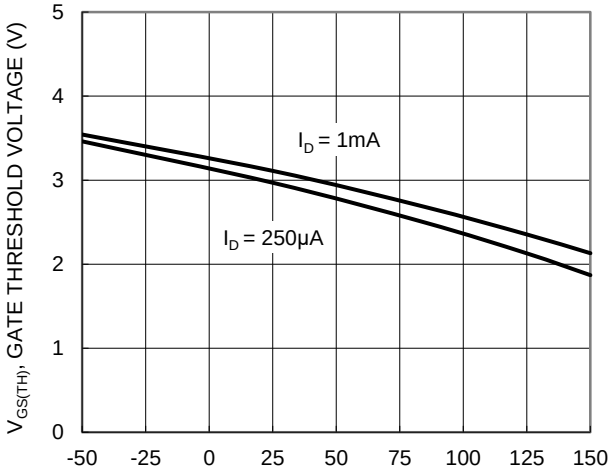


Figure 8. Gate Threshold Variation vs. Junction Temperature

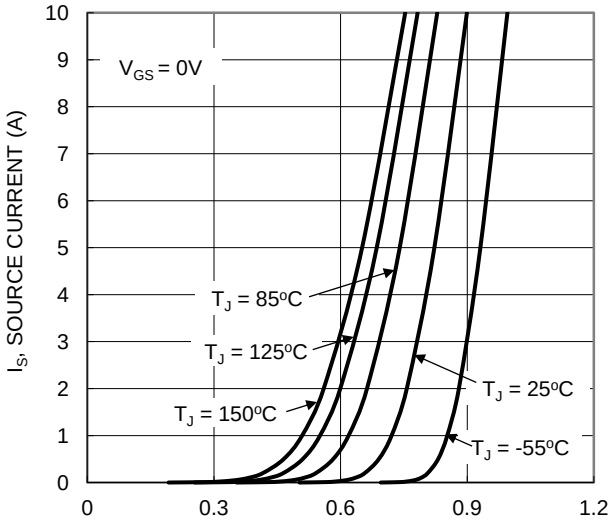


Figure 9. Diode Forward Voltage vs. Current

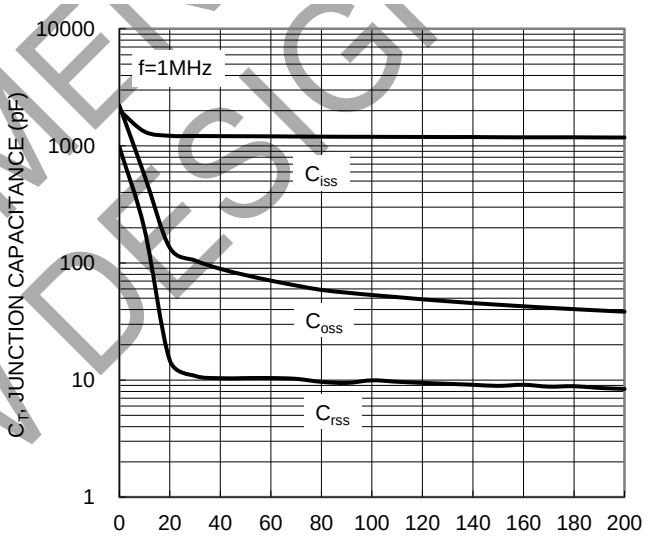


Figure 10. Typical Junction Capacitance

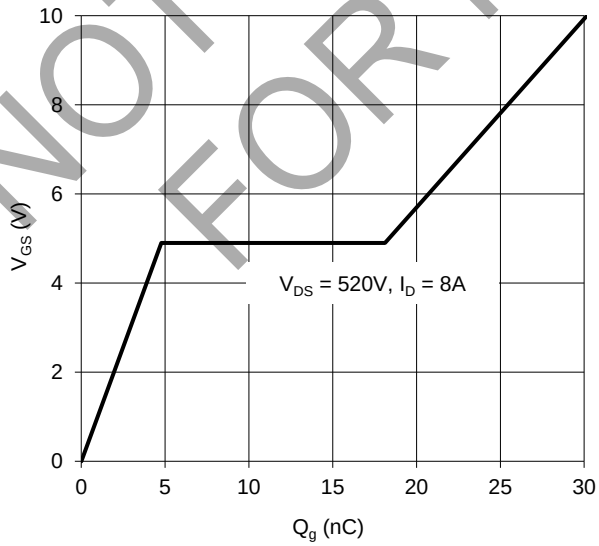


Figure 11. Gate Charge

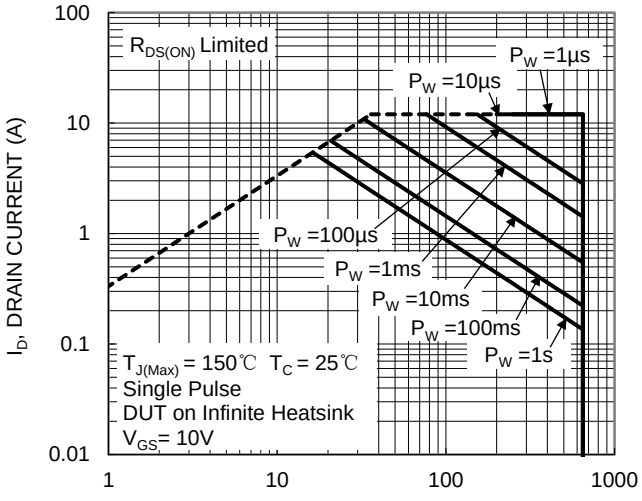


Figure 12. SOA, Safe Operation Area

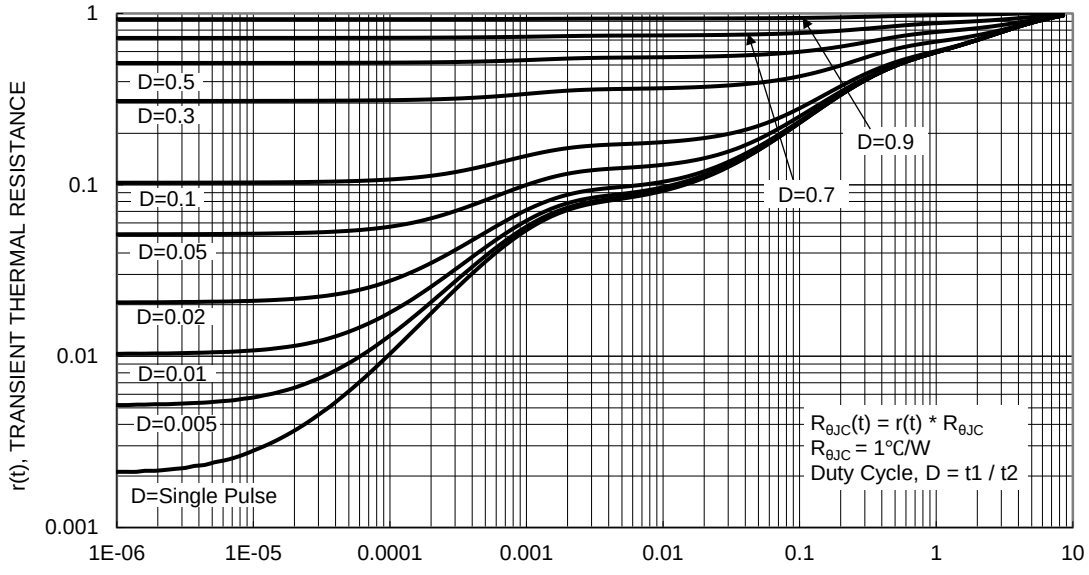
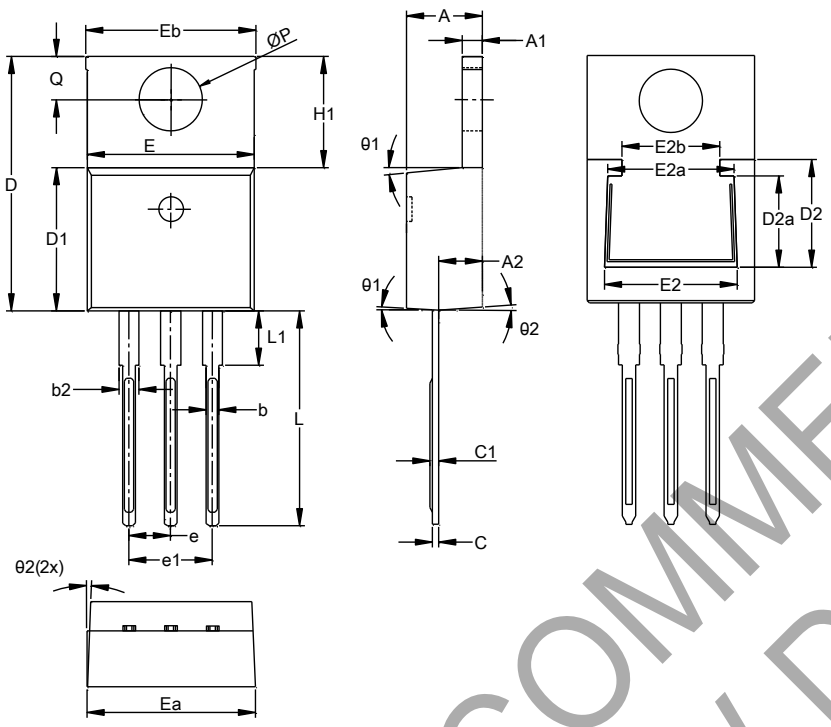


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO220AB (Type TH)



TO220AB (Type TH)			
Dim	**Min**	**Max**	**Typ**
A	4.27	4.87	4.57
A1	1.12	1.42	1.27
A2	2.39	2.99	2.69
b	0.70	1.01	0.81
b2	1.17	1.50	1.27
c	0.30	0.53	0.38
c1	0.38	0.72	0.56
D	14.60	15.40	15.00
D1	8.40	9.00	8.70
D2	5.33	6.63	6.33
D2a	4.54	5.84	5.54
e	2.54 BSC		
e1	5.08 BSC		
E	9.88	10.50	10.16
Ea	9.90	10.45	10.10
Eb	9.90	10.65	10.25
E2	7.06	8.36	8.06
E2a	6.67	7.97	7.67
E2b	4.94	6.24	5.94
H1	5.70	6.65	6.30
L	13.00	13.80	13.40
L1	-	4.10	3.75
Q	2.50	2.99	2.74
ØP	3.70	3.99	3.84
θ1	4°	10°	7°
θ2	0°	6°	3°
All Dimensions in mm			

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